

N- and P- Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
N-Channel	20	0.090 at $V_{GS} = 4.5$ V	3.28
		0.110 at $V_{GS} = 2.5$ V	2.13
		0.130 at $V_{GS} = 1.8$ V	1.50
P-Channel	- 20	0.155 at $V_{GS} = - 4.5$ V	- 2.80
		0.190 at $V_{GS} = - 2.5$ V	- 1.81
		0.220 at $V_{GS} = - 1.8$ V	- 1.15

FEATURES

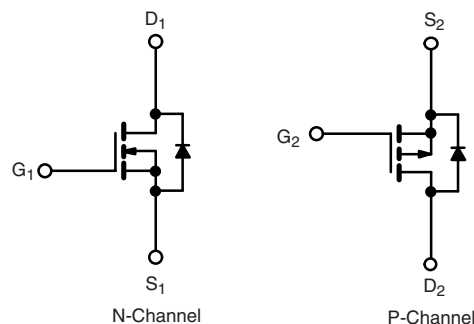
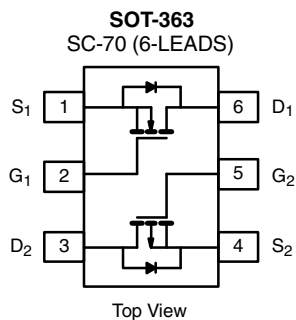
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs: 1.8 V Rated
- Thermally Enhanced SC-70 Package
- Fast Switching
- Compliant to RoHS Directive 2002/95/EC



RoHS
 COMPLIANT
 HALOGEN
FREE
 Available

APPLICATIONS

- Load Switch for Portable Devices



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		5 s	Steady State	5 s	Steady State		
Drain-Source Voltage	V_{DS}	20		- 20		V	
Gate-Source Voltage	V_{GS}	± 20		± 20		V	
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	3.28	3.03	- 2.80	- 2.58	A
		$T_A = 85$ °C	2.12	1.81	- 1.72	- 1.53	
Pulsed Drain Current	I_{DM}		9.5		- 8.5	A	
Continuous Source Current (Diode Conduction) ^a	I_S	2.61	2.48	- 1.61	-1.48	A	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	1.24	1.17	1.10	0.97	W
		$T_A = 85$ °C	0.88	0.75	0.66	0.5	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	R_{thJA}	130	170	°C/W
	Steady State		170	220	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	80	100	°C/W

Notes:

a. Surface mounted on 1" x 1" FR4 board.

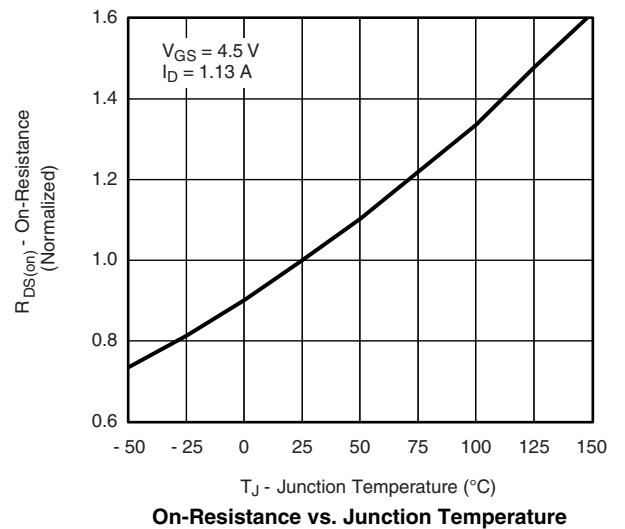
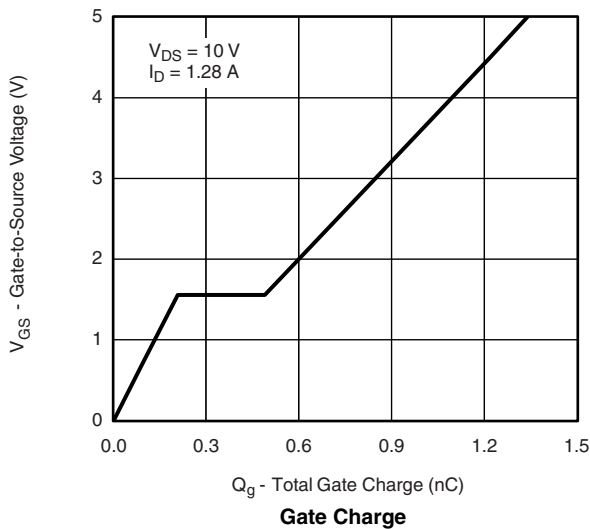
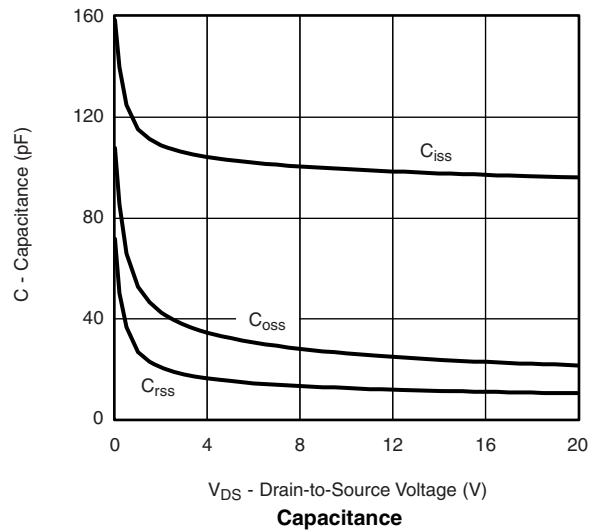
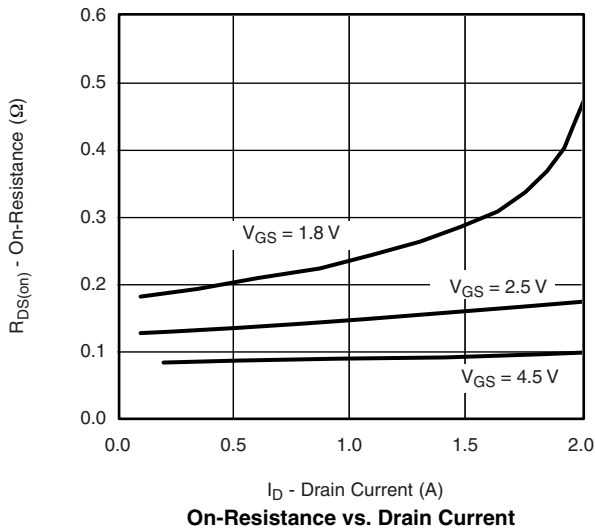
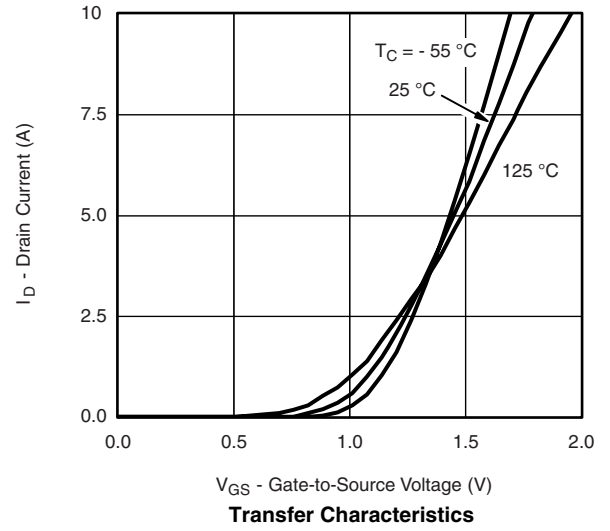
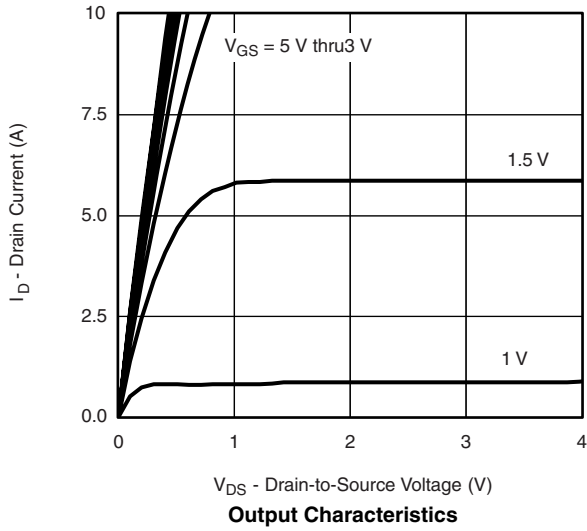
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 100\ \mu\text{A}$	N-Ch	0.45		1	V
		$V_{DS} = V_{GS}, I_D = -100\ \mu\text{A}$	P-Ch	-0.45		1	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 8\ \text{V}$	N-Ch P-Ch			± 100 ± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}$	N-Ch			1	μA
		$V_{DS} = -16\ \text{V}, V_{GS} = 0\ \text{V}$	P-Ch			-1	
		$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85\text{ }^\circ\text{C}$	N-Ch			5	
		$V_{DS} = -16\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85\text{ }^\circ\text{C}$	P-Ch			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 4.5\ \text{V}$	N-Ch	2			A
		$V_{DS} \leq -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	P-Ch	-2			
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\ \text{V}, I_D = 2.55\ \text{A}$	N-Ch		0.090		Ω
		$V_{GS} = -4.5\ \text{V}, I_D = -1.85\ \text{A}$	P-Ch		0.155		
		$V_{GS} = 2.5\ \text{V}, I_D = 1.55\ \text{A}$	N-Ch		0.110		
		$V_{GS} = -2.5\ \text{V}, I_D = -1.35\ \text{A}$	P-Ch		0.190		
		$V_{GS} = 1.8\ \text{V}, I_D = 0.50\ \text{A}$	N-Ch		0.130		
		$V_{GS} = -1.8\ \text{V}, I_D = -0.50\ \text{A}$	P-Ch		0.220		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\ \text{V}, I_D = 1.13\ \text{A}$	N-Ch		2.6		S
		$V_{DS} = -10\ \text{V}, I_D = -0.88\ \text{A}$	P-Ch		1.5		
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.48\ \text{A}, V_{GS} = 0\ \text{V}$	N-Ch		0.8	1.2	V
		$I_S = -0.48\ \text{A}, V_{GS} = 0\ \text{V}$	P-Ch		-0.8	-1.2	
Dynamic^b							
Total Gate Charge	Q_g	N-Channel $V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 2.55\ \text{A}$ P-Channel $V_{DS} = -10\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -0.88\ \text{A}$	N-Ch		1.25	2	nC
			P-Ch		1.2	1.8	
Gate-Source Charge	Q_{gs}		N-Ch		0.21		
			P-Ch		0.3		
Gate-Drain Charge	Q_{gd}		N-Ch		0.3		
			P-Ch		0.21		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 10\ \text{V}, R_L = 20\ \Omega$ $I_D \cong 0.5\ \text{A}, V_{GEN} = 4.5\ \text{V}, R_g = 6\ \Omega$ P-Channel $V_{DD} = -10\ \text{V}, R_L = 20\ \Omega$ $I_D \cong -0.5\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_g = 6\ \Omega$	N-Ch		15	25	ns
Rise Time	t_r		P-Ch		18	30	
			N-Ch		22	35	
Turn-Off Delay Time	$t_{d(off)}$		P-Ch		25	40	
			N-Ch		15	25	
Fall Time	t_f		N-Ch		12	20	
			P-Ch		12	20	
Reverse Recovery Time	t_{rr}		N-Ch		30	60	
		P-Ch		30	60		

Notes:

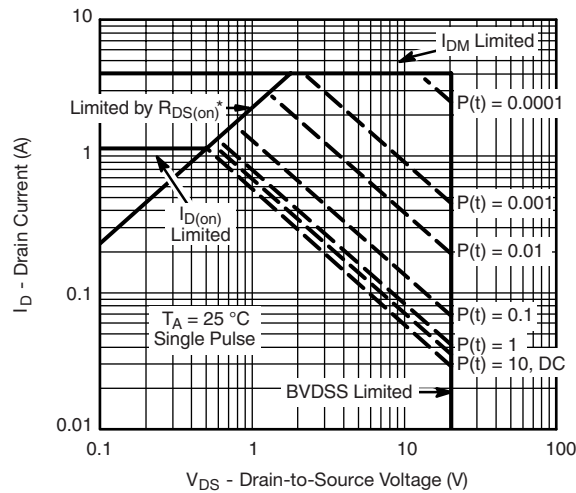
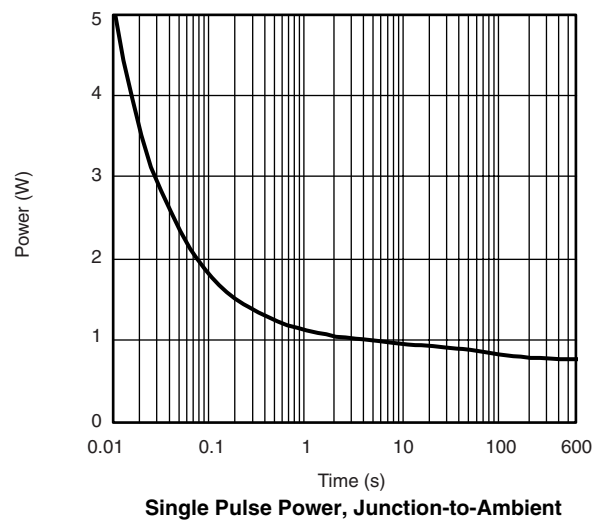
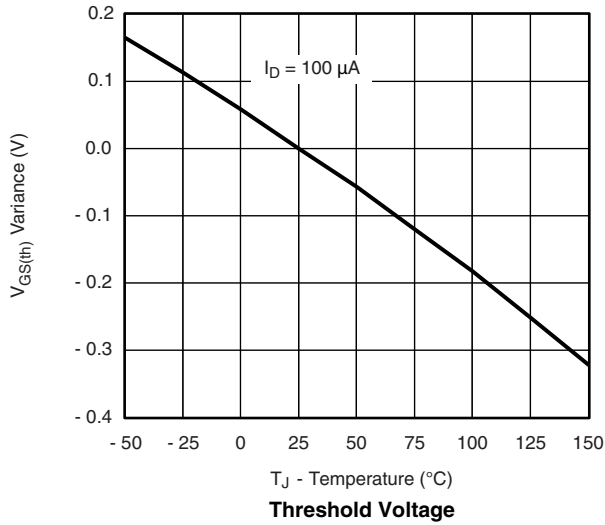
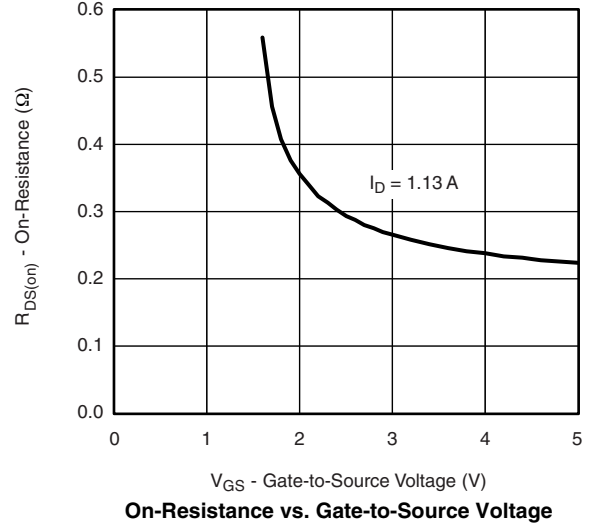
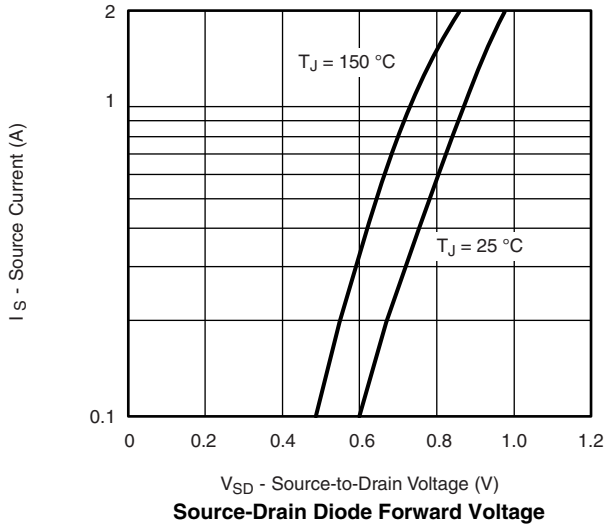
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

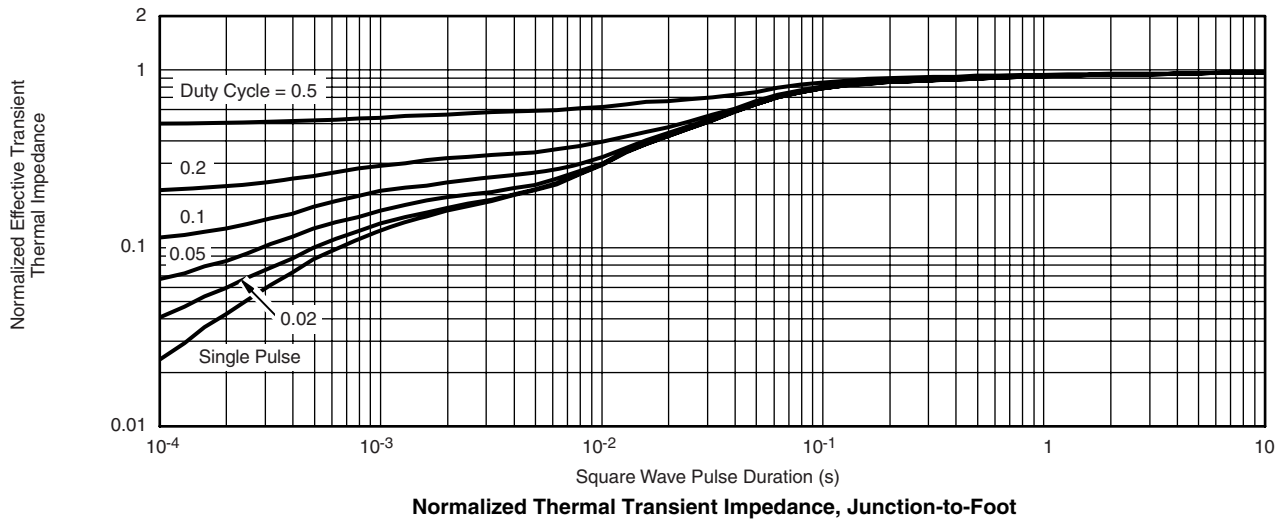
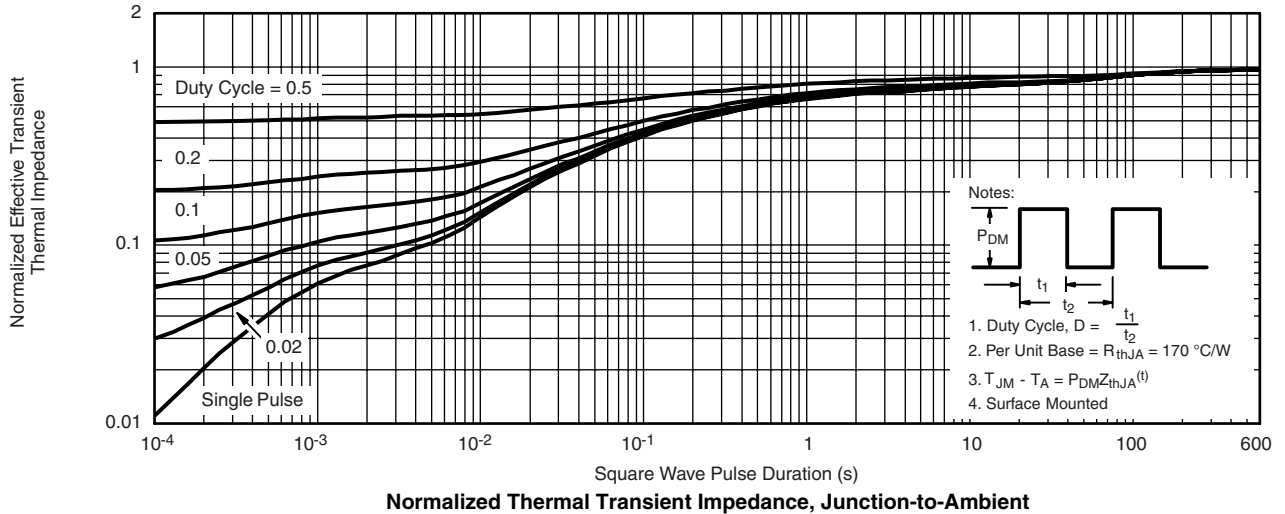


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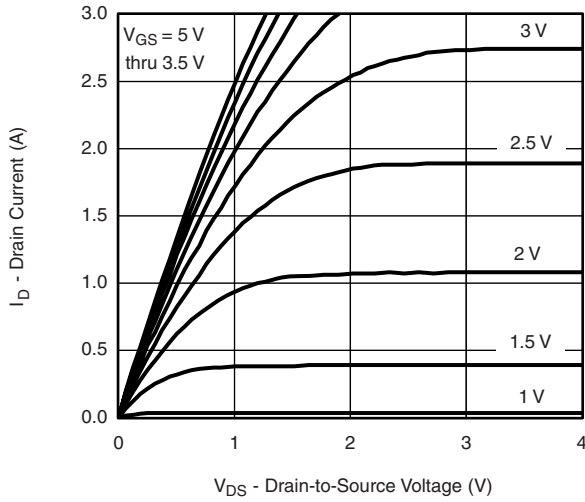


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

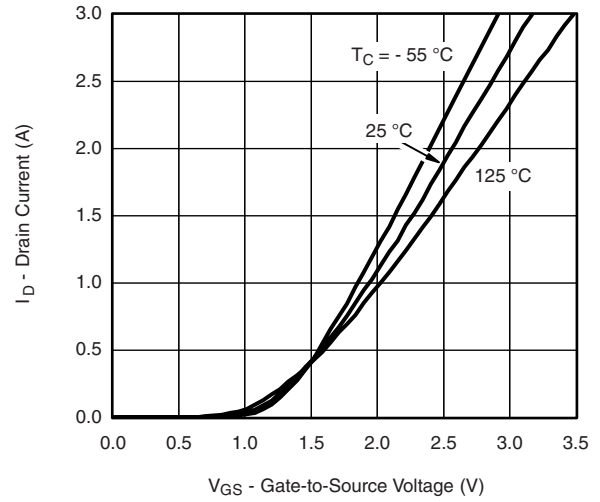
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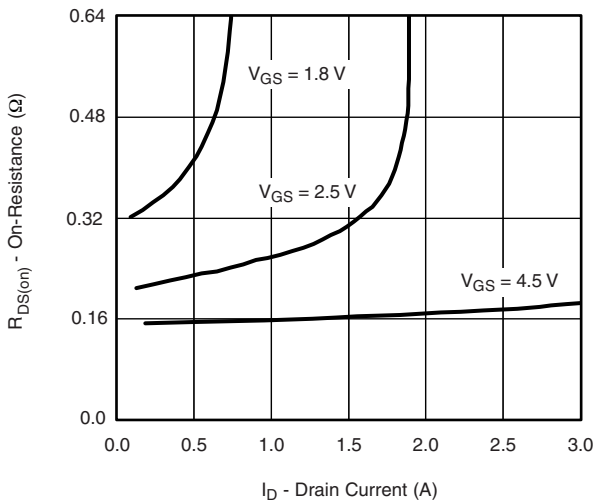
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



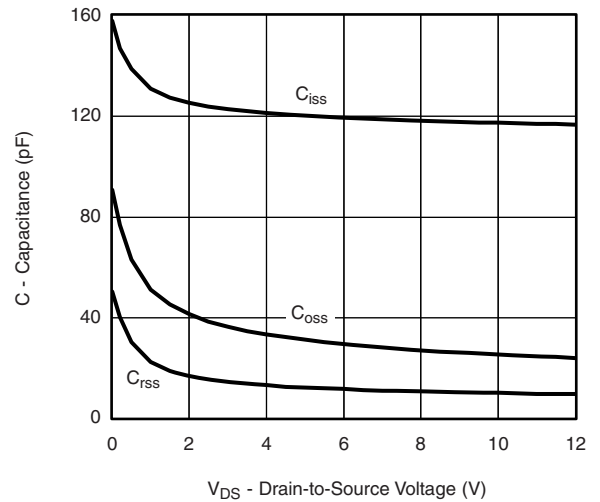
Output Characteristics



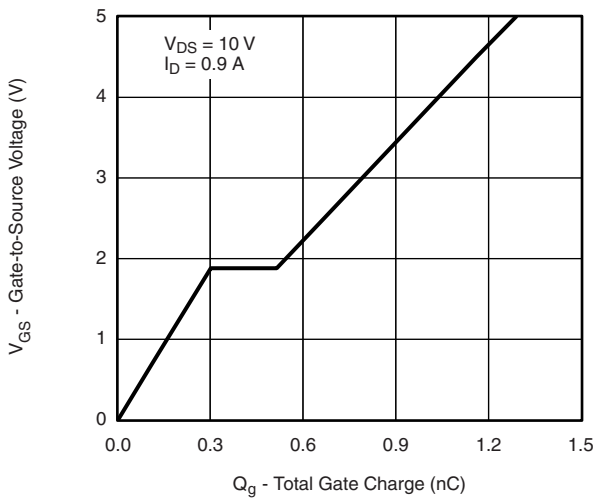
Transfer Characteristics



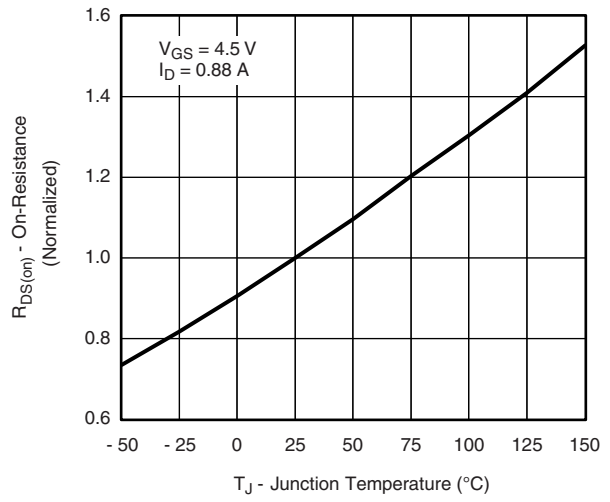
On-Resistance vs. Drain Current



Capacitance

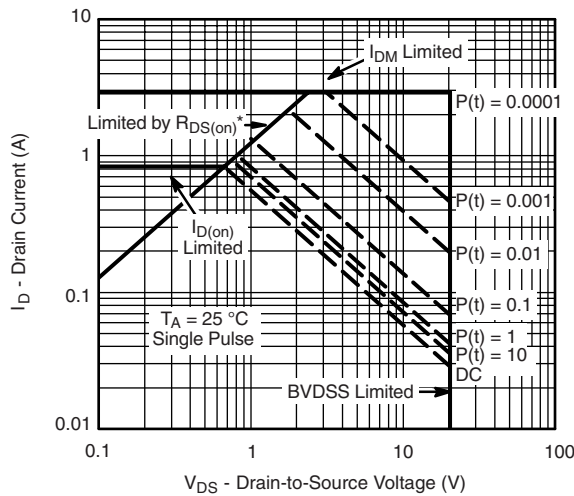
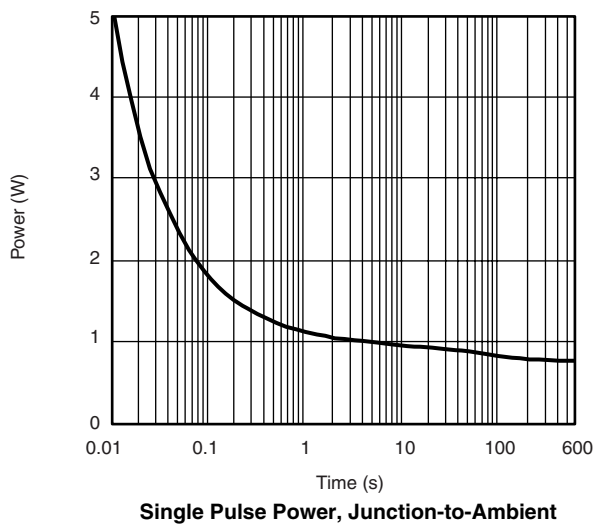
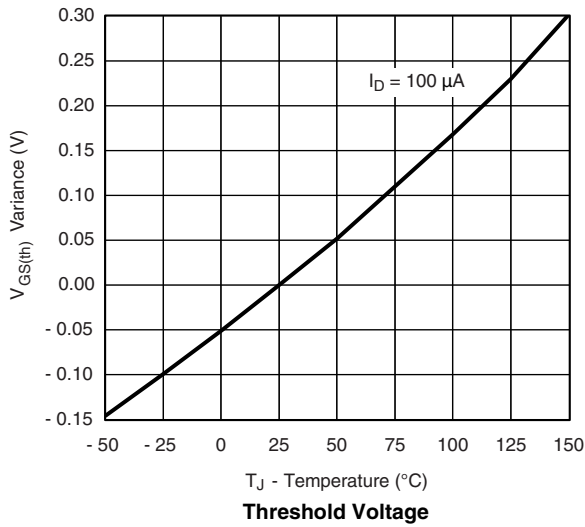
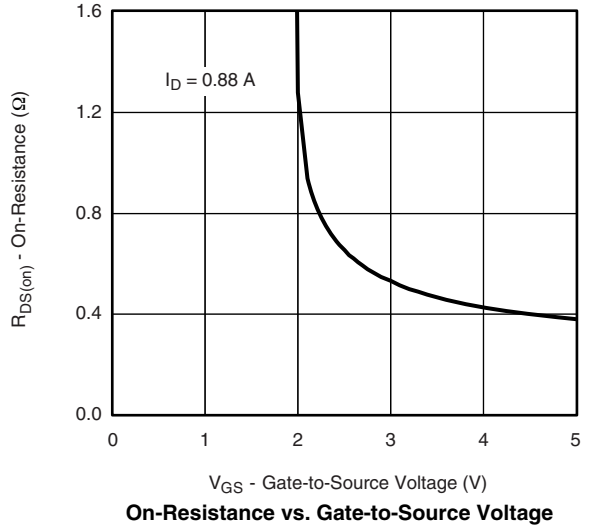
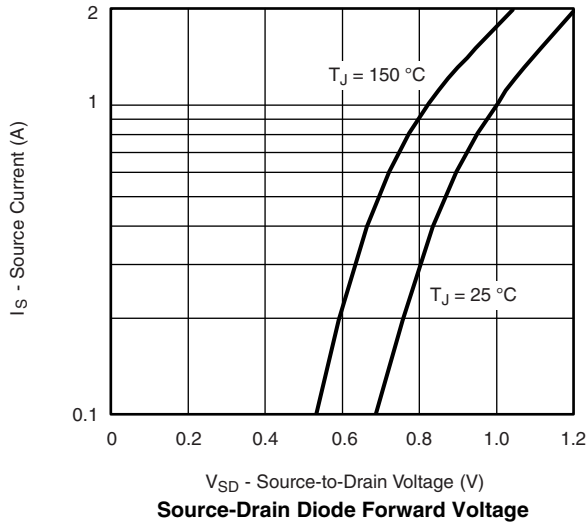


Gate Charge



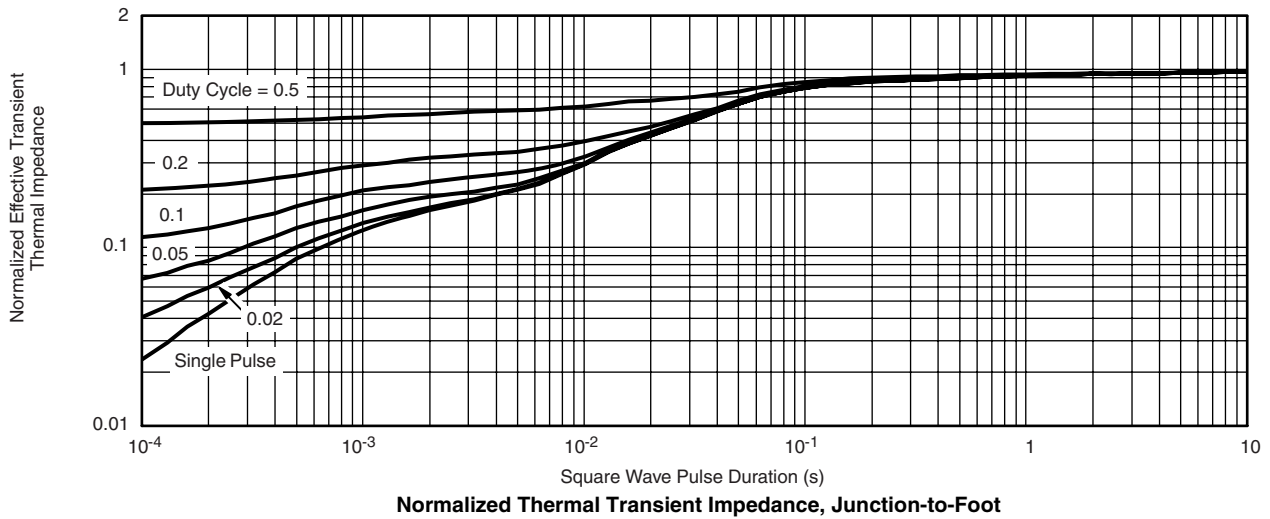
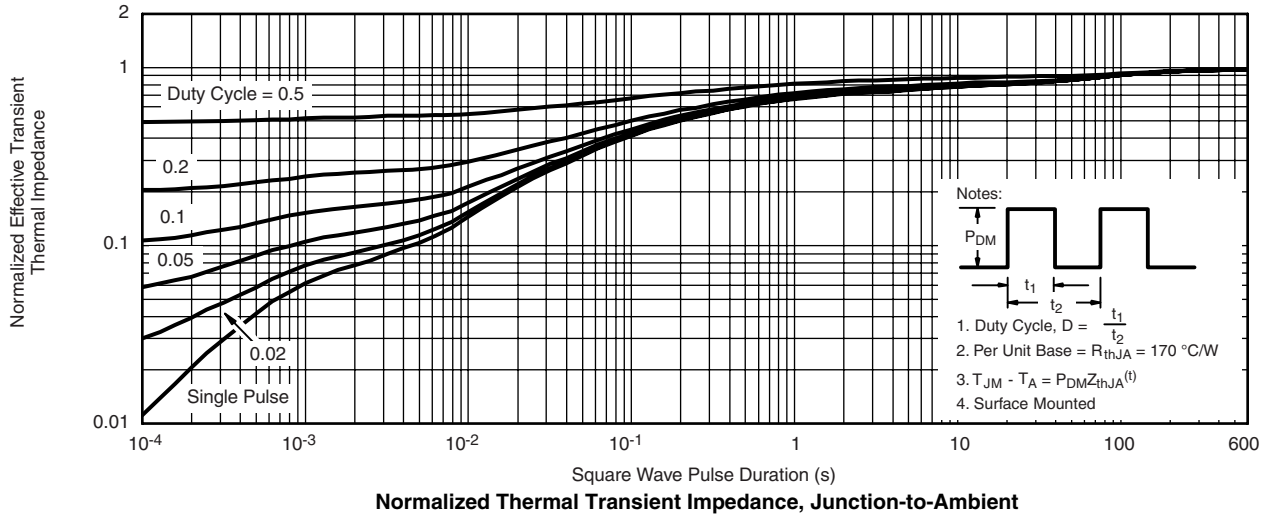
On-Resistance vs. Junction Temperature

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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